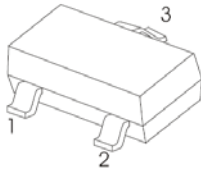
SOT-23 Plastic-Encapsulate MOSFETS

IRLML5203 P-Channel 30-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
-30V	85mΩ@-10 V	-3.0A
	145mΩ@-4.5V	

SOT－23

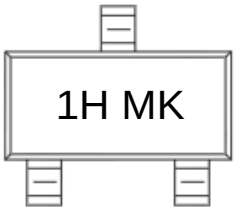


1. BASE
2. EMITTER
3. COLLECTOR

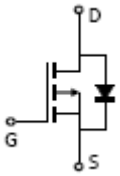
General Description

The UMW IRLML5203 uses advanced trench technology to provide excellent $R_{DS(on)}$ with low gate charge. This device is suitable for use as a load switch or in PWM applications.

MARKING



Equivalent Circuit



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	-3.0	A
Drain Current-Pulsed	I_{DM}	-24	A
Power Dissipation	P_D	300	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	417	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

SOT-23 Plastic-Encapsulate MOSFETS

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	V_{GS} = 0V, I_D =-250μA	-30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-24V,V_{GS} = 0V			-1	μA
Gate -source leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V			±100	nA
Drain-source on-resistance (note 1)	$R_{DS(on)}$	V_{GS} =-10V, I_D =-4.1A			85	mΩ
		V_{GS} =-4.5V, I_D =-3A			145	mΩ
Forward tranconductance (note 1)	g_{FS}	V_{DS} =-5V, I_D =-4A	5.5			S
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-1		-3	V
Diode forward voltage (note 1)	V_{SD}	I_S=-1A,V_{GS}=0V			-1	V
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	V_{DS} =-15V,V_{GS} =0V,f =1MHz		700		pF
Output capacitance	C_{oss}			120		pF
Reverse transfer capacitance	C_{rss}			75		pF
Switching characteristics (note 2)						
Turn-on delay time	$t_{d(on)}$	V_{GS}=-10V,V_{DS}=-15V, R_L=3.6Ω,R_{GEN}=3Ω		8.6		ns
Turn-on rise time	t_r			5.0		ns
Turn-off delay time	$t_{d(off)}$			28.2		ns
Turn-off fall time	t_f			13.5		ns

Notes:

1. Pulse test: Pulse width ≤300μs, Duty cycle ≤2%.
2. These parameter have no way to verify.

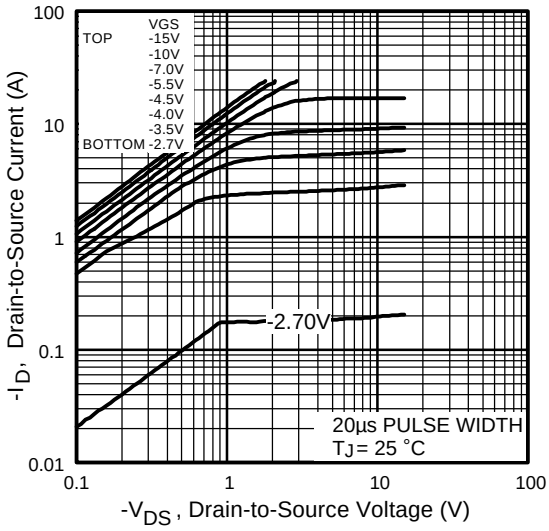


Fig 1. Typical Output Characteristics

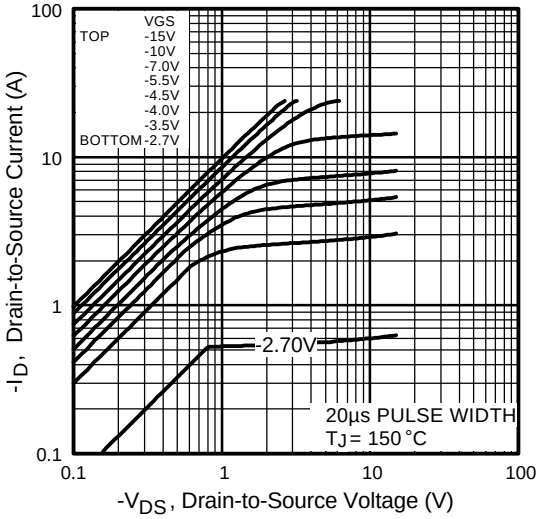


Fig 2. Typical Output Characteristics

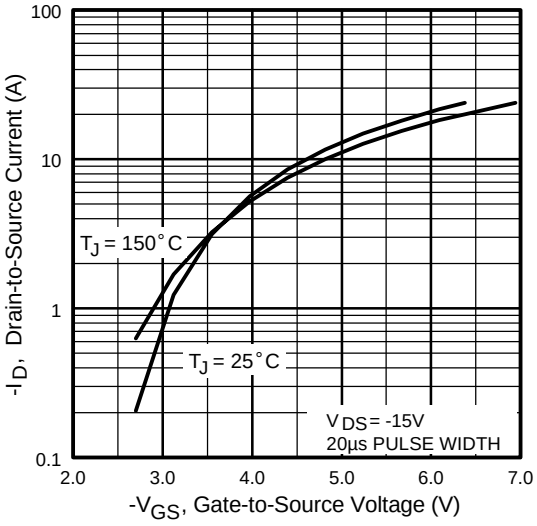


Fig 3. Typical Transfer Characteristics

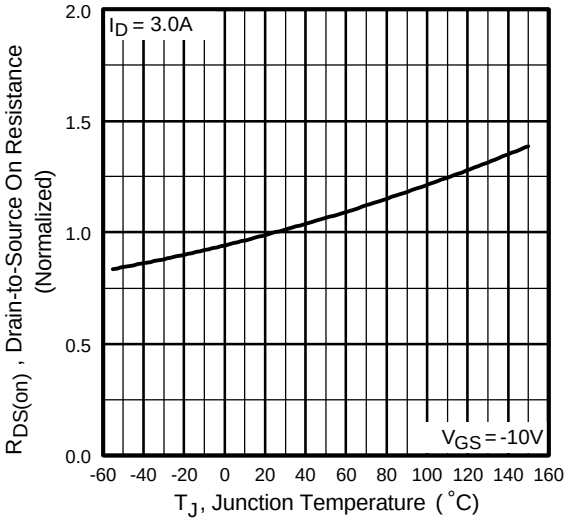


Fig 4. Normalized On-Resistance Vs. Temperature

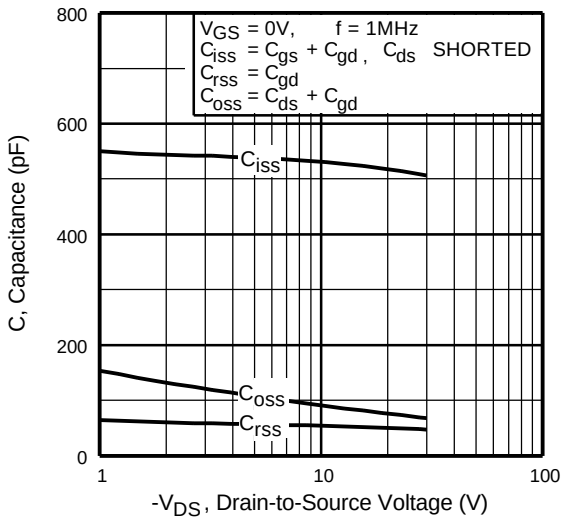


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

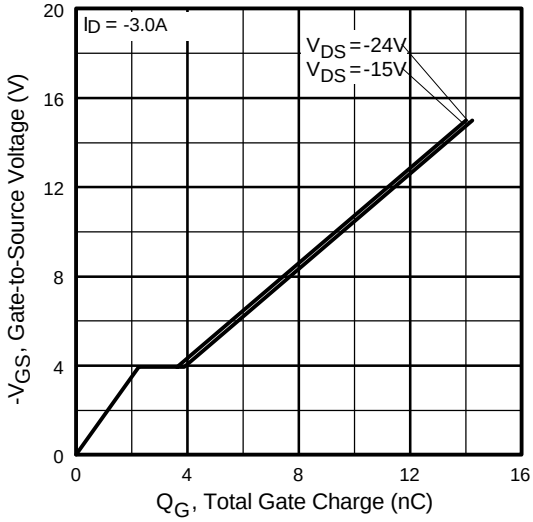


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

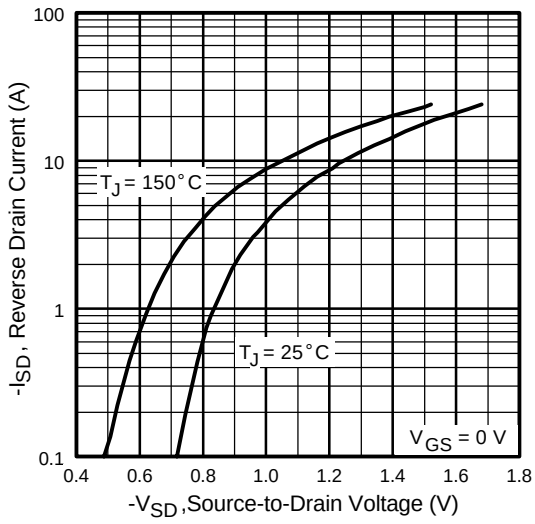


Fig 7. Typical Source-Drain Diode Forward Voltage

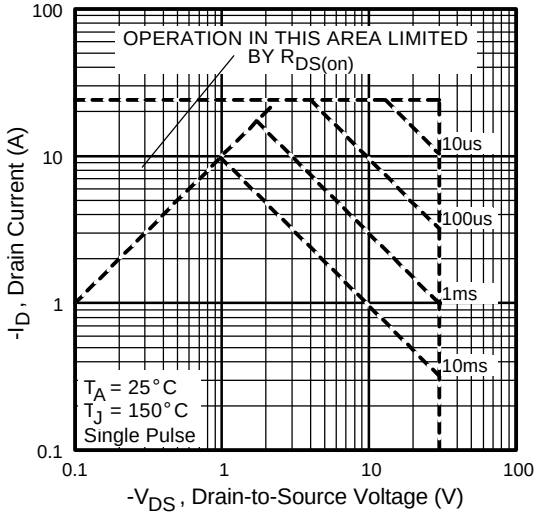


Fig 8. Maximum Safe Operating Area

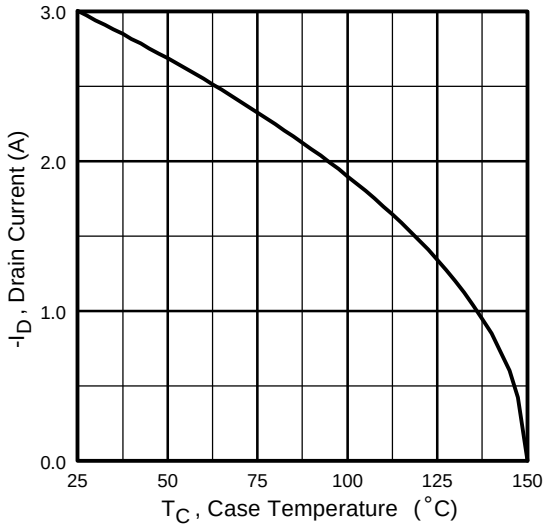


Fig 9. Maximum Drain Current Vs. Case Temperature

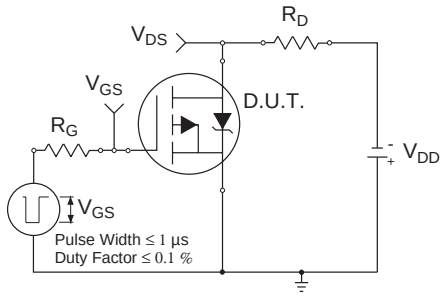


Fig 10a. Switching Time Test Circuit

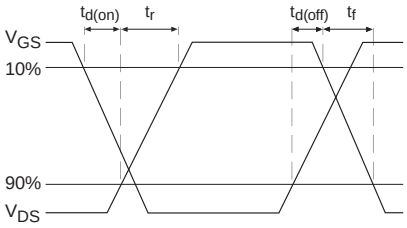


Fig 10b. Switching Time Waveforms

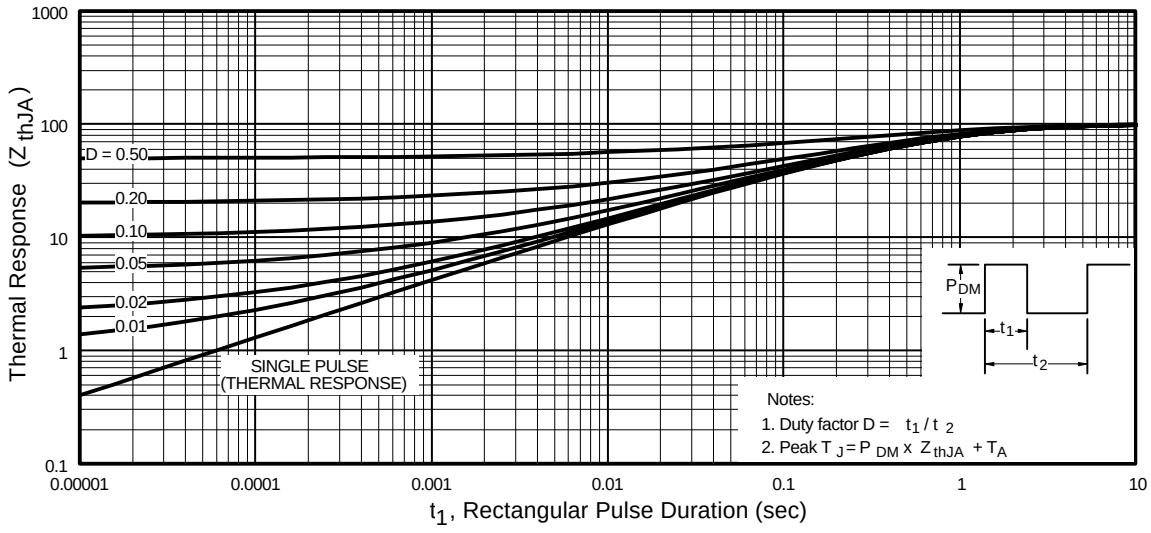


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

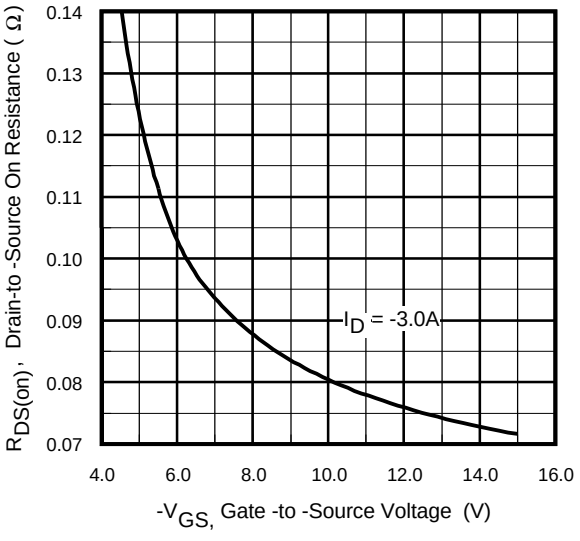


Fig 11. Typical On-Resistance Vs. Gate Voltage

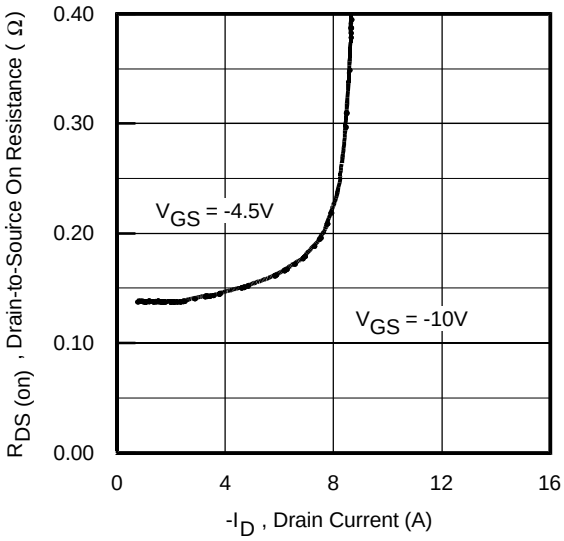


Fig 12. Typical On-Resistance Vs. Drain Current

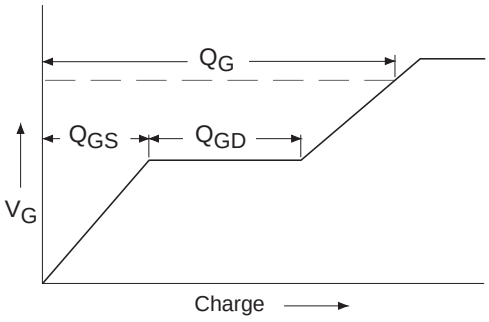


Fig 13a. Basic Gate Charge Waveform

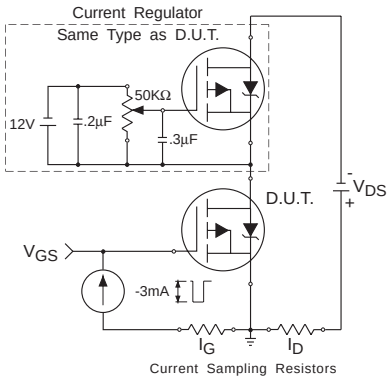


Fig 13b. Gate Charge Test Circuit

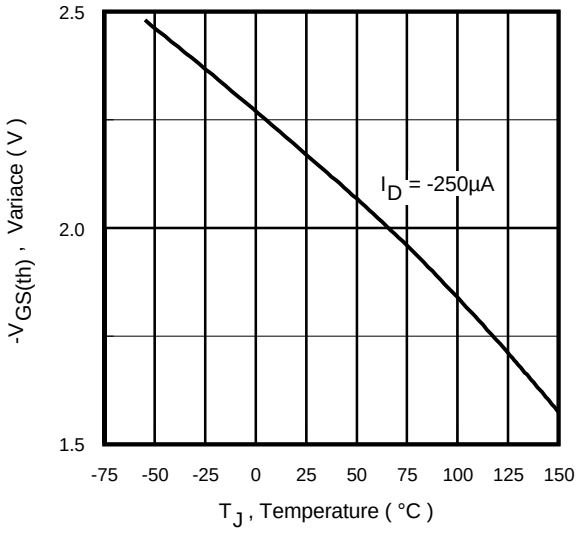


Fig 14. Threshold Voltage Vs. Temperature

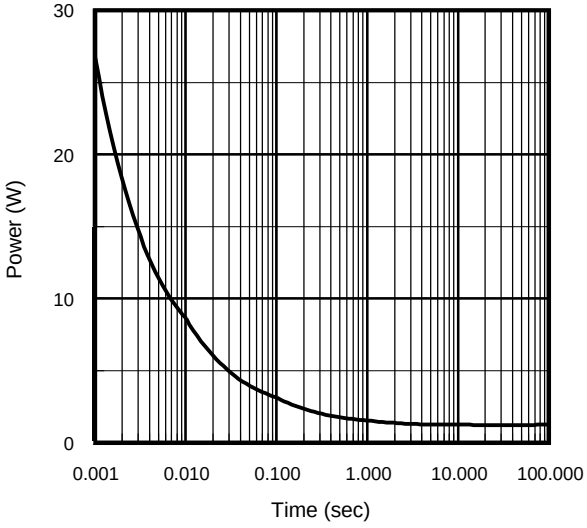
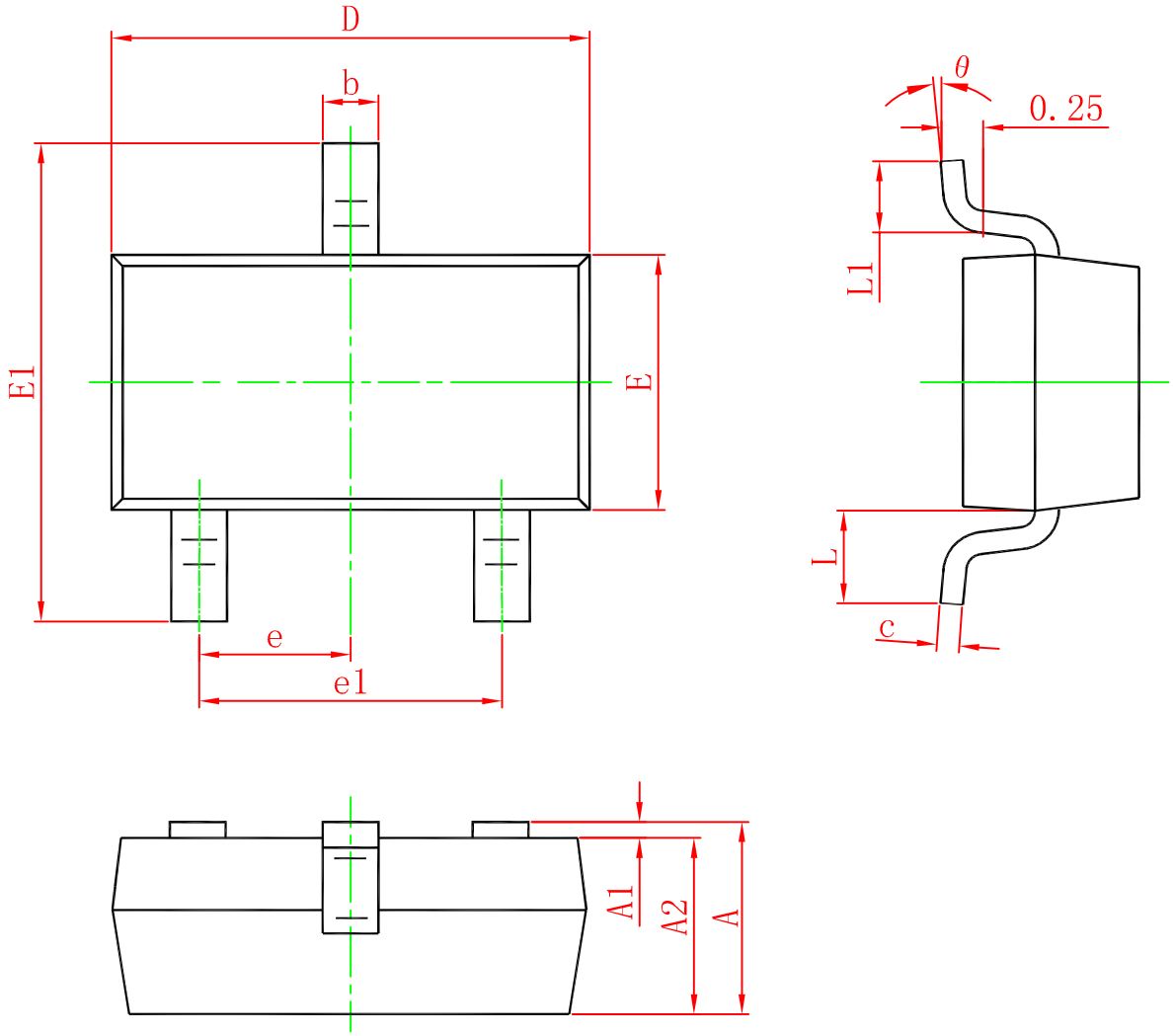


Fig 15. Typical Power Vs. Time

SOT-23 Plastic-Encapsulate MOSFETS

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°